

A SEMICONDUCTOR DEVICE HAVING A DOPED
LATTICE MATCHING LAYER AND A METHOD OF MANUFACTURE THEREFOR

ABSTRACT OF THE DISCLOSURE

The present invention provides a semiconductor device, a method of manufacture therefor, and an integrated circuit including the same. The semiconductor device may include a doped buried layer located over a doped substrate and a doped epitaxial layer located over the doped buried layer. The semiconductor device may further include a first doped lattice matching layer located between the substrate and the buried layer and a second doped lattice matching layer located between the doped buried layer and the doped epitaxial layer.